

SILICON PHOTODIODE VTP8840STR

FEATURES

- Surface mount package
- Low capacitance
- Fast response
- High shunt impedance
- Tape & reel supplied

PRODUCT DESCRIPTION

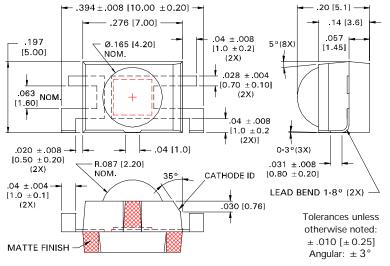
This planar silicon photodiode features a lensed, visible blocking, IR transmitting package suitable for surface mount assembly in a "side mounted" orientation.

These photodiodes exhibit performance characteristics which make them suitable for a wide range of near-IR sensing applications. Devices are shipped taped & reeled on a 24 mm embossed carrier.

ELECTRO-OPTICAL CHARACTERISTICS @ 25° C

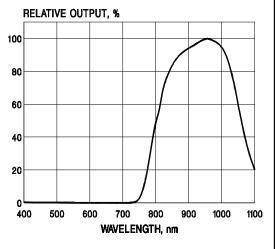
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS
SHORT CIRCUIT CURRENT @ 100 fc, 2850 K	Isc	50	60		μΑ
DARK CURRENT @ V _R = 10 V	ΙD			20	nA
SHUNT RESISTANCE @ H = 0, V = 10 mV	Rsh		0.25		GΩ
JUNCTION CAPACITANCE @ V _R = 3 V	CJ			50	pF
OPEN CIRCUIT VOLTAGE @ 100 fc, 2850 K	Voc	325			mV
ANGULAR RESPONSE (50% RESPONSE POINT)	$\theta_{1/2}$		±42		Degrees

PACKAGE DIMENSIONS inch (mm)



CHIP SIZE: .100 x .116 (2.54 x 2.94) EXPOSED ACTIVE AREA: .0082 in² (5.269 mm²)





VIP8840SIRDS Rev. A

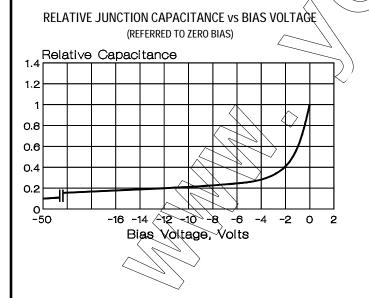
GENERAL CHARACTERISTICS

PARAMETER	SYMBOL	TYPICAL RATING	UNITS
PEAK SPECTRAL RESPONSE @ 25°C	λ_{P}	925	nm
RADIOMETRIC SENSITIVITY @ PEAK, 25°C	S _{RPK}	0.6	A / W
NOISE EQUIVALENT POWER	NEP	2.0 x 10 ⁻¹³	₩√Hz
SPECIFIC DETECTIVITY	D*	1.2 x 10 ¹²	cm /Hz /W
TEMPERATURE COEFFICIENT SHORT CIRCUIT CURRENT @ 2850 K SOURCE OPEN CIRCUIT VOLTAGE @ 2850 K SOURCE DARK CURRENT	TC I _{SC} TC Voc TC I _D	+0.22 -2.0 +15.0	%/°C mV/ C %/°C

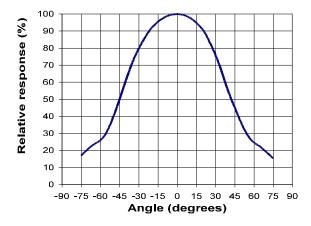
ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	RATING	UNITS
TEMPERATURE RANGE OPERATING AND STORAGE	Тамв	4 0 to +85	°C
LEAD SOLDER TEMPERATURE (1.6 mm FROM CASE, 5 SECONDS MAX.)	TLS	260°	°C
BREAKDOWN VOLTAGE @ 25°C	VBR	33	Volts
POWER DISSIPATION	P _D	150	mW

TYPICAL CHARACTERISTIC CURVES



ANGULAR RESPONSE



Specifications subject to change without prior notice. Information supplied by PerkinElmer Optoelectronics is believed to be reliable, however, no responsibility is assumed for possible inaccuracies or omissions. The user should determine the suitability of this product in his own application. No patent rights are granted to any devices or circuits described herein.

